

# UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEFARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
08/654,760	05/29/1996	MADHUKAR B. VORA	V&F-001	7867	
759	90 08/01/2002				
RONALD CRAIG FISH			EXAMINER		
FALK VESTAL 16590 OAK VII	EW CIRCLE		CRANE, S	CRANE, SARA W	
MORGAN HIL	L, CA 95037		ART UNIT	PAPER NUMBER	
			2811		
			DATE MAILED: 08/01/2002	DATE MAILED: 08/01/2002	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	7
	08/654,760	VORA, MADHUKAR B.	
Office Action Summary	Examiner	Art Unit	
	Sara W. Crane	2811	
The MAILING DATE of this communication app Period for Reply	ears on the cov rsh t with the c	corr spond nce address	
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply if NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute,  - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).  Status	6(a). In no event, however, may a reply be tim within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).	
1)⊠ Responsive to communication(s) filed on 12 A	pril 2002 .		
,	s action is non-final.		
3) Since this application is in condition for allowa closed in accordance with the practice under <i>I</i>	nce except for formal matters, pi		
Disposition of Claims	exparto quayro, 1000 o.b. 11, 1		
4) Claim(s) 1-5 is/are pending in the application.			
4a) Of the above claim(s) is/are withdraw	n from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-5</u> is/are rejected.	•		
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/or  Application Papers	election requirement.		
9) The specification is objected to by the Examiner			
10) The drawing(s) filed on is/are: a) accep		miner.	
Applicant may not request that any objection to the			
11) The proposed drawing correction filed on			
If approved, corrected drawings are required in rep			
12) The oath or declaration is objected to by the Exa	aminer.		
Priority under 35 U.S.C. §§ 119 and 120			
13) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a	a)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:			
1. Certified copies of the priority documents	s have been received.		
2. Certified copies of the priority documents	have been received in Applicati	ion No	
Copies of the certified copies of the prior application from the International Bur     See the attached detailed Office action for a list of the second	eau (PCT Rule 17.2(a)).	•	
14) ☐ Acknowledgment is made of a claim for domestic	priority under 35 U.S.C. § 119(	e) (to a provisional application).	
a) ☐ The translation of the foreign language pro 15)☐ Acknowledgment is made of a claim for domesti			
Attachment(s)	5 p.1511ty and 51 50 0.0.0. 33 120		
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal	y (PTO-413) Paper No(s) Patent Application (PTO-152)	

Art Unit: 2811

#### **DETAILED ACTION**

### Claim Rej ctions - 35 USC § 112

Claims 1-5 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Each of the independent claims uses the word "overlie" or "overlying," and it is not clear what Applicant means by this language. Note claim 1, lines 10-11, which states that the "floating gate" is "overlying" the channel region. Usually in the art, "overlie" means, literally, to "lie over." But the floating gate in, for example, Applicant's figure 2, (layer 22) does not lie *over* the channel region. It lies "next to" the channel region. All of the rest of the floating gates shown in the figures are situated similarly (next to a channel region, rather than over a channel region). Examiner assumes Applicant is using the term "overlie" to encompass a floating gate which is vertically adjacent to the channel controlled by that gate, because this is what is disclosed in the specification. The examiner is not certain, however, that this is the intention.

#### Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Art Unit: 2811

Claims 1-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. in view of Hsue et al., Sung et al., and Otani et al.

As noted in the previous Office action, the definition of "self-aligned" for this case is taken to be as stated on page 6 of the Board decision of 26 September 2001, i.e., a "self-aligned" floating gate "will not have any horizontal component on the surface of the substrate or on the bottom of the well and therefore will not extend beyond the perimeter of the trench."

With respect to the independent claims, each element of the claims, except the bit line, is clearly shown in the cover figure of Yoshida et al., where the floating gate has no horizontal component on the surface of the substrate or on the bottom of the well, and does not extend beyond the trench perimeter when viewed from above. This meets the definition of "self aligned" as quoted above. In particular, Yoshida layer 12 is an n-type source, layer 10 is a p-type channel (adjacent the floating gate), and layer 7 is an n-type drain. There are therefore "alternating" n and p type layers with a well etched through the layers. Layer 5 is identified as the "word line." See figure 2, which shows that layer 5 is a "line," and column 3, line 33, which states that layer 5 serves as a control gate (which would contact the word line in a memory cell circuit). The bit line of Yoshida et al. is shown as buried bit line 7. Hsue et al. teaches in column 1, lines 49-53, the disadvantages of a buried bit line as compared to a metal bit line overlying the word lines. Hsue et al. figures 2A-2C show the improved bit line as taught by this reference, which overlies the substrate. It would have been obvious to incorporate a bit line such as bit lines "BL" as taught by Hsue et al. in the Yoshida device, in order to gain

Art Unit: 2811

the specific advantages noted at column 1, lines 49-53, of the Hsue reference. Such a bit line overlying a word line would necessarily be spaced from the word line by an insulator, to prevent the bit line and the word line from shorting together. Sung et al. and Otani et al. are cited because each of these references also teaches the type of bit line which overlies the substrate. See the cover figure of Sung et al., and, in particular, Otani et al. figure 33 (which shows source layer 24, channel layer 25, drain layer 11, floating gate 20, "self aligned" as this term is defined above, and bit line 16 above the substrate). It would have been obvious to incorporate bit lines as taught by either of these two references in the Yoshida memory device, for the same reason as set forth in Hsue et al. as discussed above. With respect to claim 4, Hsue figure 2C shows bit line BL2 which contacts the top surface of the substrate at all points between the sidewall spacers 57, and is thus "self aligned" to the edge of the sidewall spacers. It would have been obvious to form a similar contact structure in the Yoshida device, because this would give rise to the specific desirable attributes noted above as taught by Hsue et al. A contact to "all points" as shown by Hsue figure 2C would encompass a contact to "at least some points" as recited in claim 5.

## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Crane, whose telephone number is (703) 308-4894.

The fax phone number for this Group is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist, whose telephone number is (703) 308-0956.

Sara W. Crane Primary Examiner Art Unit 2811

Art Unit: 2811